

**Features:**

- 650V Schottky Diode
- Zero Reverse Recovery Current
- High Frequency Operation
- Positive Temperature Coefficient
- Temperature independent

Switching

**Benefits:**

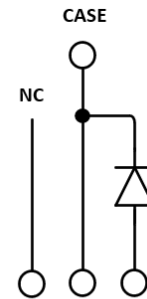
- Unipolar Rectifier
- Minimal switching loss
- Higher Efficiency
- Low cooling requirement

| Symbol                            | Value | Unit |
|-----------------------------------|-------|------|
| $V_{RRM}$                         | 650   | V    |
| $I_F$ ( $T_c=148^\circ\text{C}$ ) | 20    | A    |
| $Q_C$                             | 65    | nC   |

**Applications:**

- Switch Mode Power Supply
- Booster diodes in PFC, DC/DC
- AC/DC converters

**Outline**

**TO-247-3**
**Circuit**

**Maximum Ratings**

| Symbol      | Parameter                      | Value      | Unit             | Test Conditions   |
|-------------|--------------------------------|------------|------------------|---|
| $V_R$       | DC Peak Reverse Voltage        | 650        | V                | $T_J = 25^\circ\text{C}$  |
| $V_{RRM}$   | Repetitive Peak Reverse        | 650        | V                | $T_J = 25^\circ\text{C}$  |
| $V_{RSM}$   | Surge Peak Reverse Voltage     | 650        | V                | $T_J = 25^\circ\text{C}$  |
| $I_F$       | Continuous Forward Current     | 58         | A                | $T_C = 25^\circ\text{C}$  |
|             |                                | 26.5       |                  | $T_C = 135^\circ\text{C}$   |
|             |                                | 20         |                  | $T_C = 148^\circ\text{C}$   |
| $I_{FRM}$   | Repetitive Peak                | 176        | A                | $T_C = 25^\circ\text{C}, T_p = 10\text{ms}, \text{Half Sine Wave}$  |
|             | Forward Surge Current          | 160        |                  | $T_c = 125^\circ\text{C}, T_p = 10\text{ms}, \text{Half Sine Wave}$ |
| $I_{FSM}$   | Non-Repetitive Peak            | 236        | A                | $T_C = 25^\circ\text{C}, T_p = 10\text{ms}, \text{Half Sine Wave}$  |
|             | Forward Surge Current          | 212        |                  | $T_c = 125^\circ\text{C}, T_p = 10\text{ms}, \text{Half Sine Wave}$ |
| $P_D$       | Power Dissipation              | 200        | W                | $T_C = 25^\circ\text{C}$  |
|             |                                | 67         |                  | $T_c = 125^\circ\text{C}$   |
| $T_{J,max}$ | Operating Junction Temperature | 175        | $^\circ\text{C}$ |   |
| $T_{stg}$   | Storage Temperature Range      | -55 to 175 | $^\circ\text{C}$ |   |

### Thermal characteristics

| Symbol     | Parameter          | Min. | Typ. | Max. | Unit          |
|------------|--------------------|------|------|------|---------------|
| $R_{thJC}$ | Thermal Resistance |      | 0.75 |      | $^{\circ}C/W$ |

### Electrical Characteristics

| Symbol   | Parameter               | Value |                   |            | Unit    | Test Conditions   |
|----------|-------------------------|-------|-------------------|------------|---------|---|
|          |                         | Min.  | Typ.              | Max.       |         |   |
| $V_{DC}$ | DC Blocking Voltage     | 650   |                   |            | V       | $I_R = 100\mu A, T_J = 25^{\circ}C$   |
| $V_F$    | Forward Voltage         |       | 1.45<br>1.75      | 1.7<br>2.0 | V       | $I_F = 20A, T_J = 25^{\circ}C$<br>$I_F = 20A, T_J = 175^{\circ}C$   |
| $I_R$    | Reverse Current         |       | 2<br>50           | 50<br>300  | $\mu A$ | $V_R = 650V, T_J = 25^{\circ}C$<br>$V_R = 650V, T_J = 175^{\circ}C$   |
| $Q_C$    | Total Capacitive Charge |       | 65                |            | nC      | $I_F = 20A, dI/dt = 600A/\mu s$<br>$T_J = 25^{\circ}C, V_R = 400V$  |
| $C$      | Total Capacitance       |       | 796<br>157<br>138 |            | pF      | $V_R = 1V, T_J = 25^{\circ}C, f = 1\text{ MHz}$<br>$V_R = 200V, T_J = 25^{\circ}C, f = 1\text{ MHz}$<br>$V_R = 400V, T_J = 25^{\circ}C, f = 1\text{ MHz}$ |

### Typical Performance

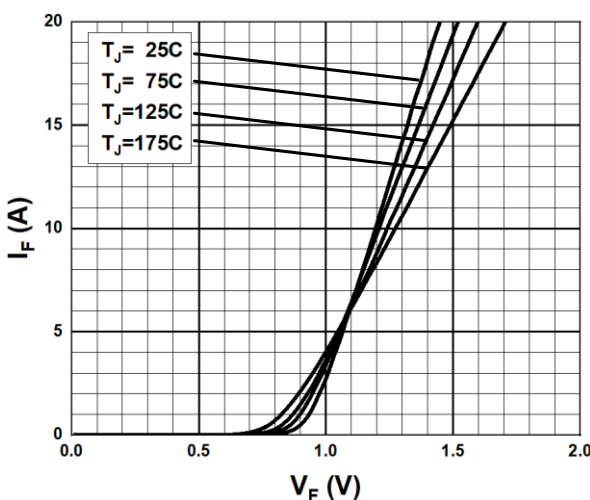


Fig. 1 Forward Characteristics

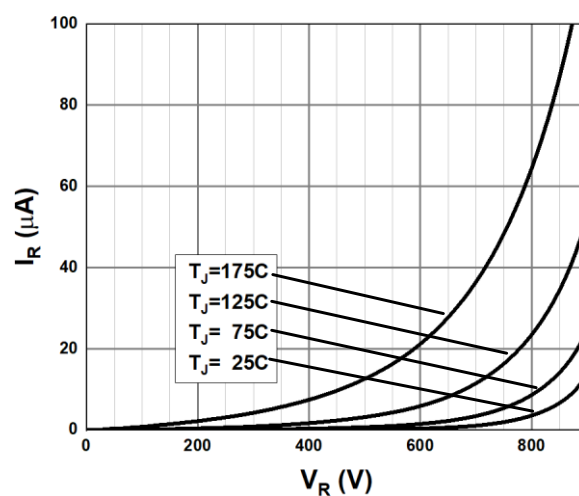
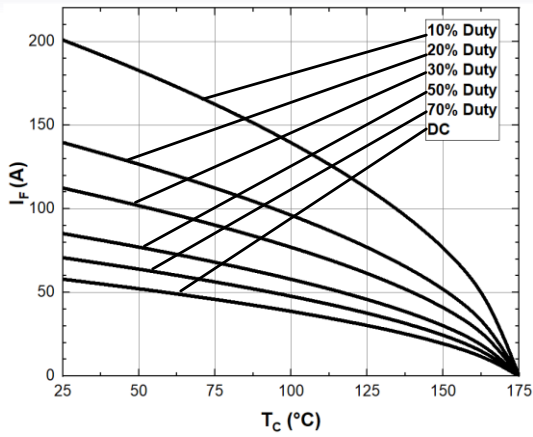
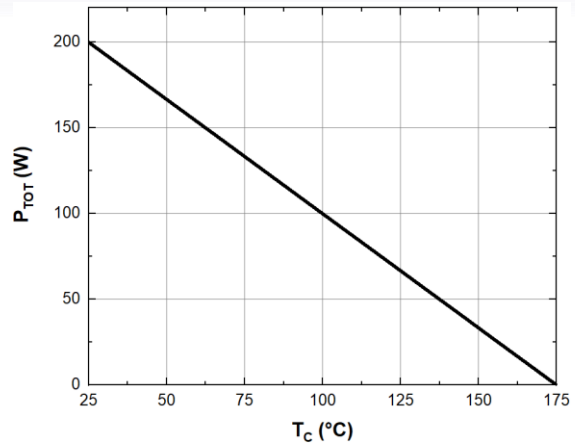


Fig. 2 Reverse Characteristics

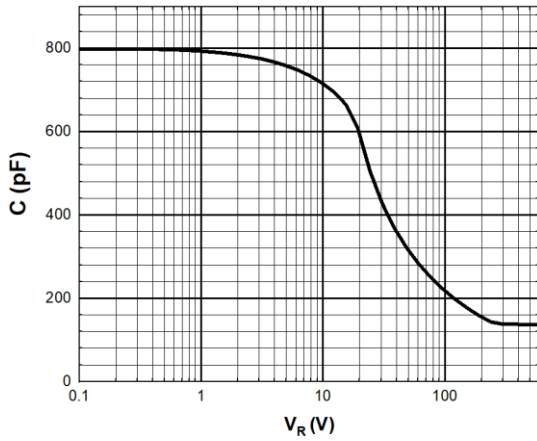
**Typical Performance**



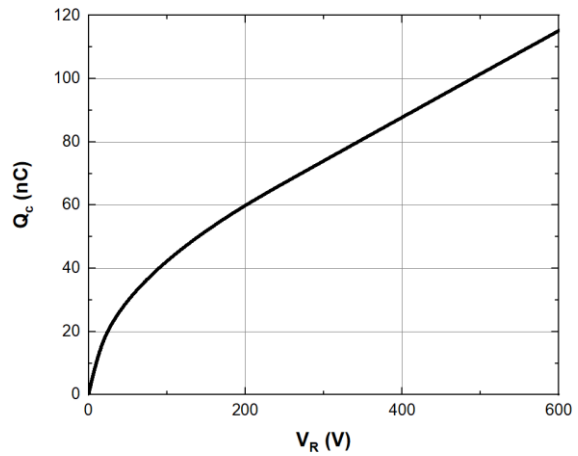
**Fig. 3 Current Derating**



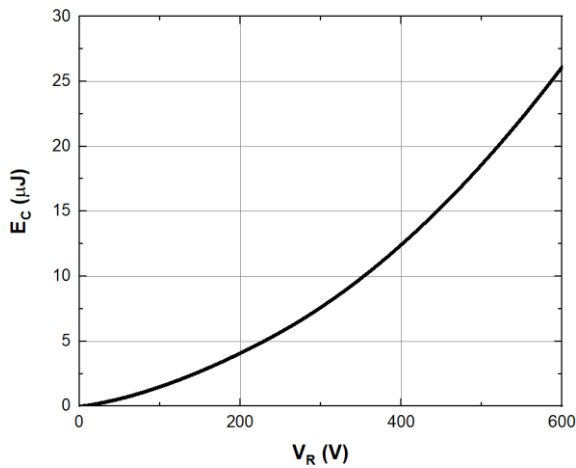
**Fig. 4 Power Derating**



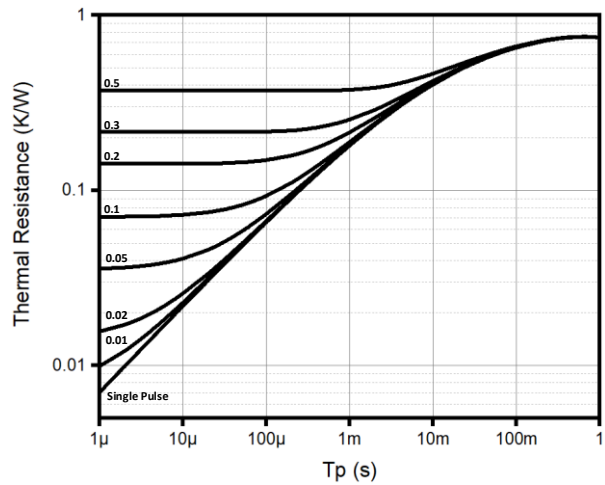
**Fig. 5 Capacitance vs. Reverse Voltage**



**Fig. 6 Recovery Charge vs. Reverse Voltage**

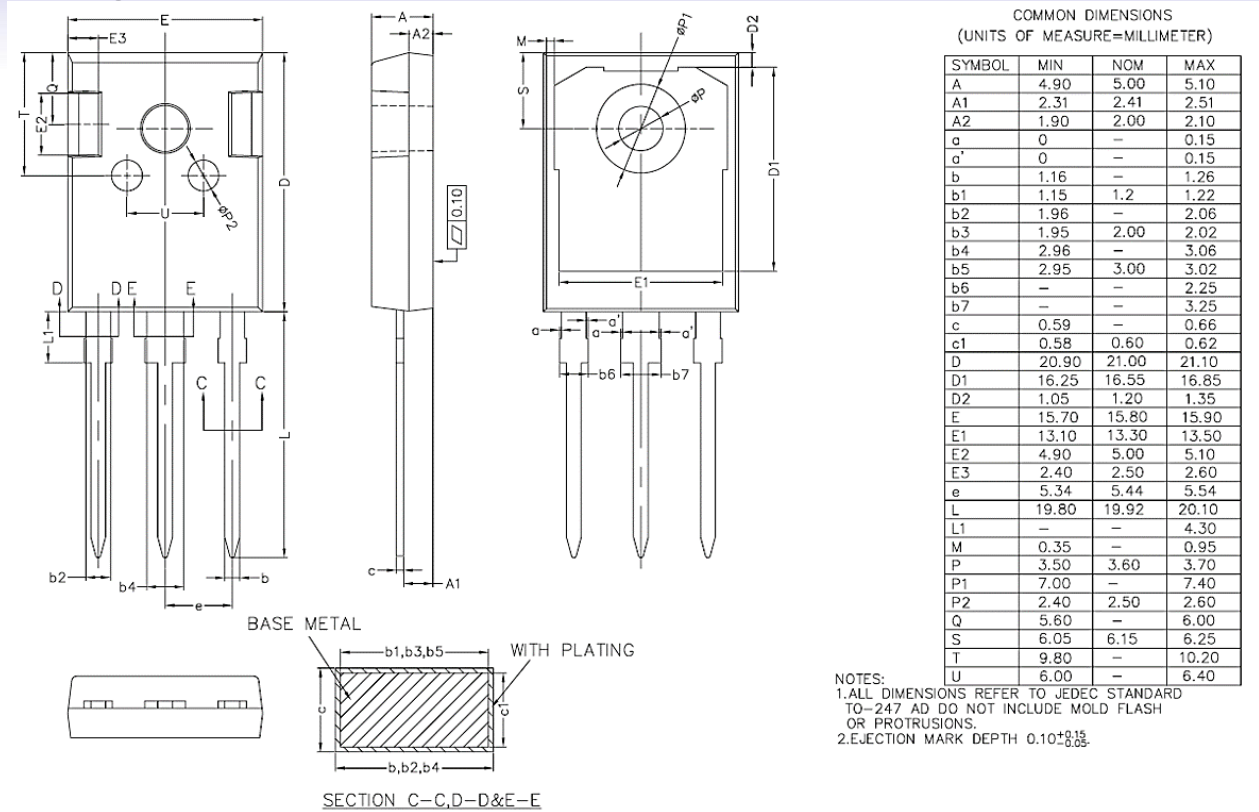


**Fig. 7 Capacitance stored Energy**



**Fig. 8 Thermal Impedance**

**Package TO-247-3 (Unit: mm)**



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